



Silicon NPN Power Ttransistors

2SD288

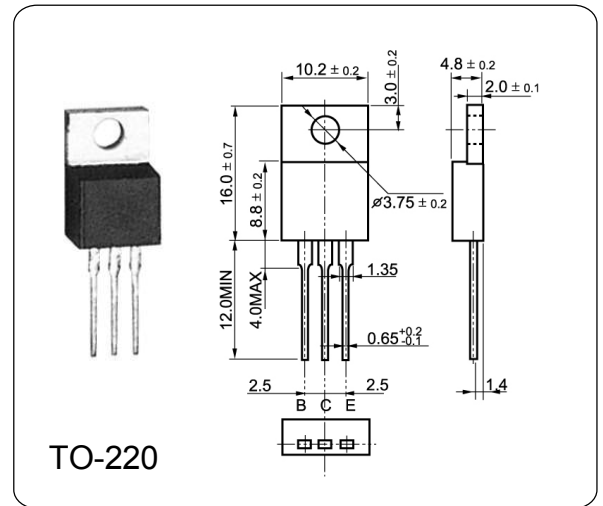


APPLICATIONS

- .Low frequency power amplifier
- .Power regulator applications

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

| Parameter | Symbol | Value | Unit |
|-------------------------------------|-----------|---------|------|
| Collector-Base Voltage | V_{CBO} | 80 | V |
| Collector-Emitter Voltage | V_{CEO} | 55 | V |
| Emitter-Base Voltage | V_{EBO} | 6.0 | V |
| Collector Current | I_C | 3.0 | A |
| Base Current | I_B | 0.3 | A |
| Total Dissipation at | P_{tot} | 25 | W |
| Max. Operating Junction Temperature | T_j | 150 | °C |
| Storage Temperature | T_{stg} | -55~150 | °C |



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------------------------------|---------------|-----------------------|------|------|------|------|
| Collector Cut-off Current | I_{CEO} | $V_{CB}=55V, I_E=0$ | — | — | 10 | uA |
| Emitter Cut-off Current | I_{EBO} | $V_{EB}=6.0V, I_C=0$ | — | — | 10 | uA |
| Collector-Emitter Sustaining Voltage | V_{CEO} | $I_C=10mA, I_B=0$ | 55 | — | — | V |
| DC Current Gain | h_{FE} | $V_{CE}=5V, I_C=0.5A$ | 40 | — | 240 | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=1.0A, I_B=100mA$ | — | — | 1.0 | V |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C=1.0A, I_B=100mA$ | — | — | 1.5 | V |

◆ h_{FE} classifications

| R | O | Y |
|-------|--------|---------|
| 40-80 | 70-140 | 120-240 |